METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, PROGRAM, AND SUBSTRATE PROCESSING APPARATUS

ABSTRACT

There is provided a technique that includes: a) supplying an adsorption inhibition gas to the substrate; b) supplying a precursor gas to the substrate; c) supplying a reaction gas to the substrate; and d) forming a film containing an element contained in the precursor gas on the substrate by performing a), b), and c) a predetermined number of times in a state where an amount of exposure of the precursor gas supplied in b) to the substrate is larger than an amount of exposure of the adsorption inhibition gas supplied in a) to the substrate.

Fig. 4